AMENDMENT

To the Claims:

1. (currently amended) A pixel structure, adapted to be disposed on a substrate, comprising:

a scan line, disposed on the substrate;

a data line, disposed on the substrate;

an active element, disposed near to an intersection of the scan line and the data line on the substrate, and electrically coupled to the scan line and the data line;

a capacitor electrode, disposed on the substrate;

a pixel electrode, disposed over the capacitor electrode and electrically coupled to the active element, wherein the pixel electrode and the capacitor electrode form a pixel storage capacitor; and ~~disposed over the substrate and electrically coupled to the active element~~

an electrical field shielding layer, disposed between the data line and the pixel electrode; and

~~a capacitor electrode, disposed between the substrate and the pixel electrode, and the capacitor electrode does not cover the data line and the scan line.~~

a transparent capacitor electrode with the capacitor electrode disposed between the transparent capacitor electrode and the pixel electrode, wherein the capacitor electrode, the transparent capacitor electrode and the pixel electrode form the pixel storage capacitor, and the capacitor electrode is made from a transparent material.

2. (original) The pixel structure of claim 1, wherein the active element comprises a low temperature polysilicon thin film transistor.

3. (original) The pixel structure of claim 2, further comprising a drain/source conductive layer, wherein the active element is electrically coupled to the data line and the pixel electrode through the drain/source conductive layer.

4. (original) The pixel structure of claim 2, further comprising a conductive layer, wherein the active element is electrically coupled to the data line through the drain/source conductive layer, and the pixel electrode is directly electrically coupled to the active element.

5. (original) The pixel structure of claim 4, wherein the conductive layer is indium tin oxide or indium zinc oxide.

Claim 6 (canceled)

7. (currently amended) The pixel structure of claim 6<u>1</u>, wherein the active element is directly electrically coupled to the transparent capacitor electrode.

8. (currently amended) The pixel structure of claim 6<u>1</u>, wherein the active element is electrically coupled to the transparent capacitor electrode through the pixel electrode.

9. (currently amended) The pixel structure of claim 6<u>1</u>, wherein the transparent capacitor electrode is made from indium tin oxide or indium zinc oxide.

10. (original) The pixel structure of claim 1, wherein the active element comprises an amorphous silicon thin film transistor.

11. (original) The pixel structure of claim 10, wherein the active element comprises:

a gate terminal, disposed on the substrate and electrically coupled to the scan line;

a channel, disposed on the gate terminal; and

a source/drain terminal, disposed on the channel and electrically coupled to the data line and the pixel electrode.

12. (original) The pixel structure of claim 1, wherein the capacitor electrode, the electrical field shielding layer and the pixel electrode are made from indium tin oxide or indium zinc oxide.

Claims 13-25. (canceled).